# Am27S12 • Am27S13

2048-Bit Generic Series Bipolar PROM

### **DISTINCTIVE CHARACTERISTICS**

- High Speed 50ns max commercial range access time
- · Excellent performance over full MIL and commercial ranges
- Highly reliable, ultra-fast programming Platinum-Silicide fuses
- High programming yield
- Low current PNP inputs
- · High current open collector and three-state outputs
- · Fast chip select
- Access time tested with N<sup>2</sup> patterns
- · Pin for pin replacements for industry standard products
- Common Generic PROM series electrical characteristics and simple programming procedures.

### **GENERIC SERIES CHARACTERISTICS**

The Am27S12 and Am27S13 are members of an Advanced PROM series incorporating common electrical characteristics and programming procedures. All parts in this series are produced with a fusible link at each memory location storing a logic LOW and can be selectively programmed to a logic HIGH by applying appropriate voltages to the circuit.

All parts are fabricated with AMD's fast programming highly reliable Platinum-Silicide Fuse technology. Utilizing easily implemented programming (and common programming personality card sets) these products can be rapidly programmed to any customized pattern. Extra test words are pre-programmed during manufacturing to insure extremely high field programming yields, and produce excellent parametric correlation.

Platinum-Silicide was selected as the fuse link material to achieve a well controlled melt rate resulting in large nonconductive gaps that ensure very stable long term reliability. Extensive operating testing has proven that this low-field, large-gap technology offers the best reliability for fusible link PROMs.

Common design features include active loading of all critical AC paths regulated by a built-in temperature and voltage compensated bias network to provide excellent parametric performance over MIL supply and temperature ranges. Selective feedback techniques have been employed to minimize delays through all critical paths producing the fastest speeds possible from Schottky processed PROMs.

#### ORDERING INFORMATION

_	Package Type	Temperature Range	Order Number		
		Open Collectors	•		
	Hermetic DIP	0°C to +75°C	AM27S12DC		
	Hermetic DIP	-55°C to +125°C	AM27S12DM		
•	Hermetic Flat Pak	-55°C to +125°C	AM27S12FM		
Three-State Outputs					
	Hermetic DIP	0°C to +75°C	AM27S13DC		
	Hermetic DIP	-55°C to +125°C	AM27S13DM		
	Hermetic Flat Pak	-55°C to +125°C	AM27S13FM		

#### FUNCTIONAL DESCRIPTION

The Am27S12 and Am27S13 are high speed electrically programmable Schottky read only memories. Organized in the industry standard 512 x 4 configuration, they are available in both open collector Am27S12 and three-state Am27S13 output versions. After programming, stored information is read on outputs  $O_0 - O_3$  by applying unique binary addresses to  $A_0 - A_8$  and holding the chip select input,  $\overline{CS}$ , at a logic LOW. If the chip select input goes to a logic HIGH,  $O_0 - O_3$  go to the off or high impedance state.



# Am27S12 • Am27S13

# MAXIMUM RATINGS (Above which the useful life may be impaired)

Storage Temperature	−65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential (Pin 16 to Pin 8) Continuous	-0.5V to +7.0V
DC Voltage Applied to Outputs (Except During Programming)	-0.5V to +V <sub>CC</sub> max.
DC Voltage Applied to Outputs During Programming	21V
Output Current into Outputs During Programming (Max. Duration of 1 sec.)	200mA
DC Input Voltage	-0.5V to +5.5V
DC Input Current	-30mA to +5mA

# **DPERATING RANGE**

COM'L	Am27S12XC, Am27S13XC	$T_A = 0^{\circ}C$ to $+75^{\circ}C$	$V_{CC} = 5.0V \pm 5\%$
MIL	Am27S12XM, Am27S13XM	$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$	$V_{CC} = 5.0V \pm 10\%$

# ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE (Unless Otherwise Noted) RELIMINARY DATA

arameters	Description	Test Conditions		Min.	Typ. (Note 1)	Max.	Units	
V <sub>OH</sub> (Am27S13 only)	Output HIGH Voltage	V <sub>CC</sub> = MIN., I <sub>OH</sub> = -2.0mA V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>			2.4			Volts
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = MIN V <sub>IN</sub> = V <sub>IH</sub>	, I <sub>OL</sub> = 16mA or V <sub>IL</sub>				0.45	Volts
V <sub>IH</sub>	Input HIGH Level	Guaranteed voltage for a	input logical H Il inputs	IIGH	2.0			Volts
VIL	Input LOW Level	Guaranteed voltage for a	input logical L Il inputs	.ow			0.8	Volts
ΊL	Input LOW Current	V <sub>CC</sub> = MAX	., V <sub>IN</sub> = 0.45	V		-0.010	-0.250	mA
Чн	Input HIGH Current	V <sub>CC</sub> ≈ MAX	., V <sub>IN</sub> = 2.7V				25	μA
Ч	Input HIGH Current	V <sub>CC</sub> = MAX., V <sub>IN</sub> = 5.5V					1.0	mA
I <sub>SC</sub> (Am27S13 onlý)	Output Short Circuit Current	V <sub>CC</sub> = MAX., V <sub>OUT</sub> = 0.0V (Note 2)			-20	-40	90	mA
ICC	Power Supply Current	All inputs = GND V <sub>CC</sub> = MAX.				100	130	mA
VI	Input Clamp Voltage	V <sub>CC</sub> = MIN., I <sub>IN</sub> = -18mA				-1.2	Volts	
				V <sub>O</sub> = 4.5V	4.5V		40	
ICEX	Output Leakage Current	$V_{CC} = MAX.$ $V_{\overline{CS}} = 2.4V$	Am27S13	Am27S13 Vo = 2.4V			40	μA
			only	V <sub>O</sub> = 0.4V			-40	
c <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 2.0V @ f = 1 MHz (Note 3)				4		
с <sub>оит</sub>	Output Capacitance	V <sub>OUT</sub> = 2.0V @ f = 1 MHz (Note 3)				8		p۳

Votes: 1. Typical limits are at V<sub>CC</sub> = 5.0 V and T<sub>A</sub> = 25°C.
2. Not more than one output should be shorted at a time. Duration of the short circuit should not be more than one second.

3. These parameters are not 100% tested, but are periodically sampled.

# SWITCHING CHARACTERISTICS OVER OPERATING RANGE PRELIMINARY DATA

	Description	Test Conditions	Тур	. Max			
Parameter			5V 25°C	COM'L	MIL	Units	
tAA	Address Access Time		30	50	60	ns	
<sup>t</sup> EA	Enable Access Time	AC Test Load (See Notes 1-3)	15	25	30	ns	
t <sub>ER</sub>	Enable Recovery Time	(000 10:03 10)	15	25	30	ns	

Notes: 1. t<sub>AA</sub> is tested with switch S<sub>1</sub> closed and C<sub>L</sub> = 30pF.

2. For open collector outputs,  $t_{EA}$  and  $t_{ER}$  are tested with S<sub>1</sub> closed to the 1.5V output level.  $C_L$  = 30pF.

3. For three state outputs,  $t_{EA}$  is tested with  $C_L = 30$  pF to the 1.5V level;  $S_1$  is open for high impedance to HIGH tests and closed for high impedance to LOW tests.  $t_{ER}$  is tested with  $C_L = 5$  pF. HIGH to high impedance tests are made with  $S_1$  open to an output voltage of  $V_{OH} = 0.5V$ ; LOW to high impedance tests are made with  $S_1$  closed to the  $V_{OL} + 0.5V$  level.



# PROGRAMMING

The Am27S12 and Am27S13 are manufactured with a conductive Platinum-Silicide link at each bit location. The output of the memory with the link in place is LOW. To program the device, the fusible links are selectively opened.

The fusible links are opened one at a time by passing current through them from a 20 volt supply which is applied to one memory output after the  $\overline{CS}$  input is at a logic HIGH. Current is gated through the addressed fuse by raising the  $\overline{CS}$  input from a logic HIGH to 15 volts. After 50  $\mu$ sec, the 20 volt supply is removed, the chip enabled, and the output level sensed to determine if the link has opened. Most links will open within 50  $\mu$ sec. Occasionally a link will be stronger and require additional programming cycle. The recommended duration of additional programming periods is 5 msec. If a link has not opened after a total elapsed programming time of 400 msec, further programming of the device should not be attempted. Successive links are programmed in the same manner until all desired bit locations have been programmed to the HIGH level.

Typical current into an output during programming will be approximately 140mA until the fuse link is opened, after which the current drops to approximately 40mA. Current into the  $\overline{CS}$  pin when it is raised to 15 volts is typically 1.5mA.

The memories may become hot during programming due to the large currents being passed. Programming cycles should not be applied to one device more than 5 seconds to avoid heat damage. If this programming time is exceeded, all power to the chip including  $V_{CC}$  should be removed for a period of 5 seconds after which programming may be resumed.

When all programming has been completed, the data content of the memory should be verified by sequentially reading all words. Occasionally this verification will show that an extra undesired link has been fused. Should this occur, immediately check the programming equipment to make sure that all device pins are firmly contacting the programming socket, that the input signal levels exhibit sufficient noise margins, and that the programming voltages are within the specified limits. All of these conditions must be maintained during programming. AMD PROMs are thoroughly tested to minimize unwanted fusing; fusing extra bits is generally related to programming equipment problems.

PROGRAMMI	ING PARAMETERS				
Parameter	Description	Min.	Max.	Units	
VCCP	V <sub>CC</sub> During Programming	5.0	5.5	Volts	
VIHP	Input HIGH Level During Programming	2.4	5.5	Volts	
VILP	Input LOW Level During Programming	0.0	0.45	Volts	
V <sub>CSP</sub>	CS Voltage During Programming	14.5	15.5	Volts	
V <sub>OP</sub>	Output Voltage During Programming	19.5	20.5	Volts	
VONP	Voltage on Outputs Not to be Programmed	0	V <sub>CCP</sub> +0.3	Volts	
IONP	Current into Outputs Not to be Programmed		20	mA	
d(V <sub>OP</sub> )/dt	Rate of Output Voltage Change	20	250	V/µsec	
d(V <sub>CS</sub> )/dt	Rate of CS Voltage Change	100	1000	V/µsec	
	Programming Period – First Attempt	50	100	μsec	
ιp	Programming Period - Subsequent Attempts	5.0	15	msec	

Notes: 1. All delays between edges are specified from completion of the first edge to beginning of the second edge; i.e., not to the midpoints.
 2. Delays t<sub>1</sub>, t<sub>2</sub>, t<sub>3</sub> and t<sub>4</sub> must be greater than 100 ns; maximum delays of 1 μsec are recommended to minimize heating during programming.

3. During ty, a user defined period, the output being programmed is switched to the load R and read to determine if additional pulses are required.

4. Outputs not being programmed are connected to VONP through resistor R which provides output current limiting.







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#### **PROGRAMMING EQUIPMENT**

Generic programming boards and device adapters are available from the sources listed below. In each case, the programming boards are used in these manufacturer's automatic programmers to program all AMD generic series bipolar PROMs; individual adapters are required for each basic part type in the series.

SOURCE AND LOCATION	Data I/O Corp P.O. Box 308 Issaquah, Wash. 98027	Pro-Log Corp. 2411 Garden Road Monterey, Ca. 93940
PROGRAMMER MODEL(S)	Model 5, 7 and 9	M900 and M920
AMD GENERIC BIPOLAR PROM PERSONALITY BOARD	909-1286-1	PM9058
Am27S12 • Am27S13 ADAPTERS AND CONFIGURATOR	715-1408-2	PA16-5 and 512 x 4 (L)

#### **OBTAINING PROGRAMMED UNITS**

Programmed devices may be purchased from your distributor or Advanced Micro Devices. The program data should be submitted in the form of a punched paper tape and must be accompanied by a written truth table. The punched tape can be delivered with your order or may be transmitted over a TWX machine or time-sharing terminal. ASCII BPNF is our preferred paper tape format.

#### ASCII BPNF

An example of an ASCII tape in the BPNF format is shown below. They can be punched on any Teletype<sup>®</sup> or on a TWX or Telex machine. The format chosen provides relatively good error detection. Paper tapes must consist of:

- 1. A leader of at least 25 rubouts.
- 2. The data patterns for all 512 words, starting with word 0, in the following format:
  - a. Any characters, including carriage return and line feed, except "B".
  - b. The letter "B", indicating the beginning of the data word.
  - c. A sequence of four Ps or Ns, starting with output O<sub>3</sub>.
  - d. The letter "F", indicating the finish of the data word.
  - Any text, including carriage return and line feed, except the letter "B".

Truth tables are also acceptable, but are much less desirable especially for larger density PROMs. Submission of a truth table requires the generation of a punched paper tape at the distributor or factory resulting in longer lead times, greater possibility of error, and higher cost.

3. A trailer of at least 25 rubouts.

A P is a HIGH logic level = 2.4 volts. An N is a LOW logic level = 0.4 volts.

A convenient pattern to use for the data words is to prefix the word (or every few words with the word number, then type the data word, then a comment, then carriage return and line feed as shown below. There must be no characters between the B and the F except for the four Ps and Ns. If an error is made in a word, the entire word must be cancelled with rubouts back to the letter B, then the word re-typed beginning with the B.

When TWXing your tape, be sure the tape is in even parity. Parity is not necessary if the tape is mailed.



# APPLYING THE Am27S12 AND Am27S13

The Am27S12 and Am27S13 can be used with a high speed counter to form a pico-controller for microprogrammed systems. A typical application is illustrated below wherein a multiplexer, under control of one of the PROMs, is continuously sensing the CONDITIONAL TEST INPUTS. When the selected condition occurs, a HIGH signal will result at the mul-

tiplexer output causing a predetermined branch address to be loaded into the parallel inputs of the counters on the next clock pulse. The counter then accesses the preprogrammed data or control information sequence from the Am27S12 or Am27S13 PROMs.

